

62mm C-Serien Modul mit schnellem Trench/Feldstop IGBT3 und Emitter Controlled High Efficiency Diode  
62mm C-series module with fast trench/fieldstop IGBT3 and Emitter Controlled High Efficiency diode

## IGBT, 逆变器 / IGBT, Inverter

### 最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	1200	V
连续集电极直流电流 Continuous DC collector current	$T_C = 80^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$ $T_C = 25^{\circ}\text{C}, T_{vj\max} = 150^{\circ}\text{C}$	$I_{C\text{nom}}$ $I_C$	200 295	A A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	400	A
总功率损耗 Total power dissipation	$T_C = 25^{\circ}\text{C}, T_{vj\max} = 150$	$P_{\text{tot}}$	1050	W
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

### 特征值 / Characteristic Values

			min.	typ.	max.	
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 200\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 200\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,70 1,90	2,15	V V
栅极阈值电压 Gate threshold voltage	$I_C = 8,00\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{G\text{Eth}}$	5,0	5,8	6,5 V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	1,90		$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{G\text{int}}$	3,8		$\Omega$
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{\text{ies}}$	14,0		nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{\text{res}}$	0,50		nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$		5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$		400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 3,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{on}}$	0,16 0,17		$\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{on}} = 3,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_r$	0,04 0,045		$\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 3,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_{d\text{off}}$	0,45 0,52		$\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{G\text{off}} = 3,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$t_f$	0,10 0,16		$\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 4000\text{ A}/\mu\text{s}$ $R_{G\text{on}} = 3,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{\text{on}}$	10,0 15,0		mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 200\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 4500\text{ V}/\mu\text{s}$ $R_{G\text{off}} = 3,6\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{\text{off}}$	16,5 25,0		mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 900\text{ V}$ $V_{CE\text{max}} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 125^{\circ}\text{C}$		$I_{SC}$	800		A
结 - 外壳热阻 Thermal resistance, junction to case	每个 IGBT / per IGBT		$R_{thJC}$		0,12	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个 IGBT / per IGBT $\lambda_{\text{Paste}} = 1\text{ W}/(\text{m}\cdot\text{K})$ / $\lambda_{\text{grease}} = 1\text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,03		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40	125	$^{\circ}\text{C}$

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**二极管, 逆变器 / Diode, Inverter**  
**最大额定值 / Maximum Rated Values**

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1200	V
连续正向直流电流 Continuous DC forward current		$I_F$	200	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1 \text{ ms}$	$I_{FRM}$	400	A
$I^2t$ -值 $I^2t$ - value	$V_R = 0 \text{ V}, t_P = 10 \text{ ms}, T_{vj} = 125^{\circ}\text{C}$	$I^2t$	7800	$\text{A}^2\text{s}$

**特征值 / Characteristic Values**

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$ $I_F = 200 \text{ A}, V_{GE} = 0 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$V_F$	1,65 1,65	2,15	V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 200 \text{ A}, -di_F/dt = 4000 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$I_{RM}$	150 190		A A
恢复电荷 Recovered charge	$I_F = 200 \text{ A}, -di_F/dt = 4000 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$Q_r$	20,0 36,0		$\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 200 \text{ A}, -di_F/dt = 4000 \text{ A}/\mu\text{s} (T_{vj}=125^{\circ}\text{C})$ $V_R = 600 \text{ V}$ $V_{GE} = -15 \text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$	$E_{rec}$	9,00 17,0		mJ mJ
结 - 外壳热阻 Thermal resistance, junction to case	每个二极管 / per diode		$R_{thJC}$		0,20	K/W
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个二极管 / per diode $\lambda_{\text{Paste}} = 1 \text{ W}/(\text{m}\cdot\text{K}) / \lambda_{\text{grease}} = 1 \text{ W}/(\text{m}\cdot\text{K})$		$R_{thCH}$	0,06		K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj \text{ op}}$	-40	125	$^{\circ}\text{C}$

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**模块 / Module**

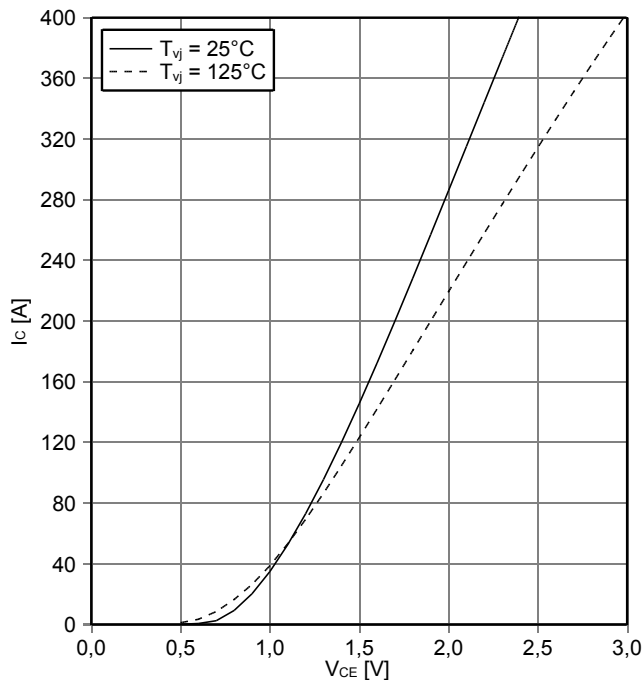
绝缘测试电压 Isolation test voltage	RMS, f = 50 Hz, t = 1 min.	V <sub>ISOL</sub>	2,5		kV
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		Al <sub>2</sub> O <sub>3</sub>		
爬电距离 Creepage distance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		29,0 23,0		mm
电气间隙 Clearance	端子- 散热片 / terminal to heatsink 端子- 端子 / terminal to terminal		23,0 11,0		mm
相对电痕指数 Comperative tracking index		CTI	> 400		
min.    typ.    max.					
外壳 - 散热器热阻 Thermal resistance, case to heatsink	每个模块 / per module $\lambda_{\text{Paste}} = 1 \text{ W/(m}\cdot\text{K)} / \lambda_{\text{grease}} = 1 \text{ W/(m}\cdot\text{K)}$	R <sub>thCH</sub>	0,01		K/W
杂散电感,模块 Stray inductance module		L <sub>sCE</sub>	20		nH
模块引线电阻,端子-芯片 Module lead resistance, terminals - chip	T <sub>C</sub> = 25°C, 每个开关 / per switch	R <sub>CC+EE'</sub>	0,70		mΩ
储存温度 Storage temperature		T <sub>stg</sub>	-40	125	°C
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,00	-	6,00 Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	2,5	-	5,0 Nm
重量 Weight		G	340		g

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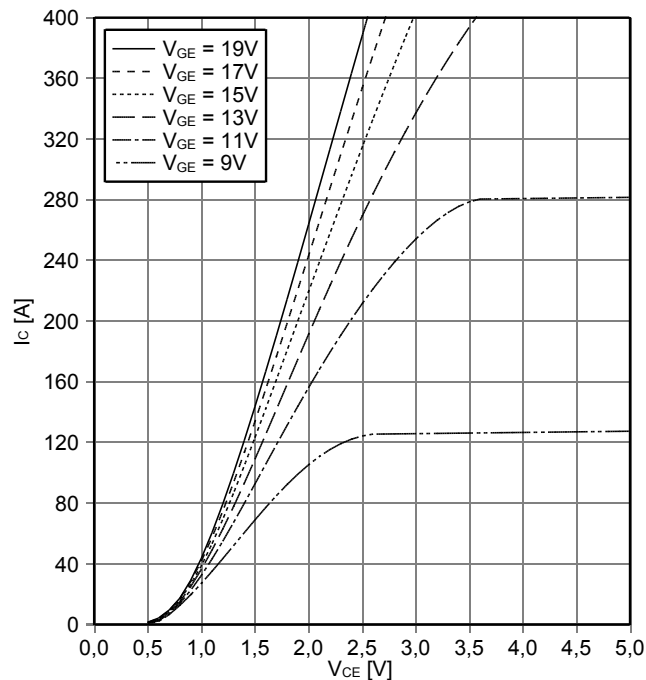
输出特性 IGBT, 逆变器 (典型)  
output characteristic IGBT, Inverter (typical)

$I_c = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



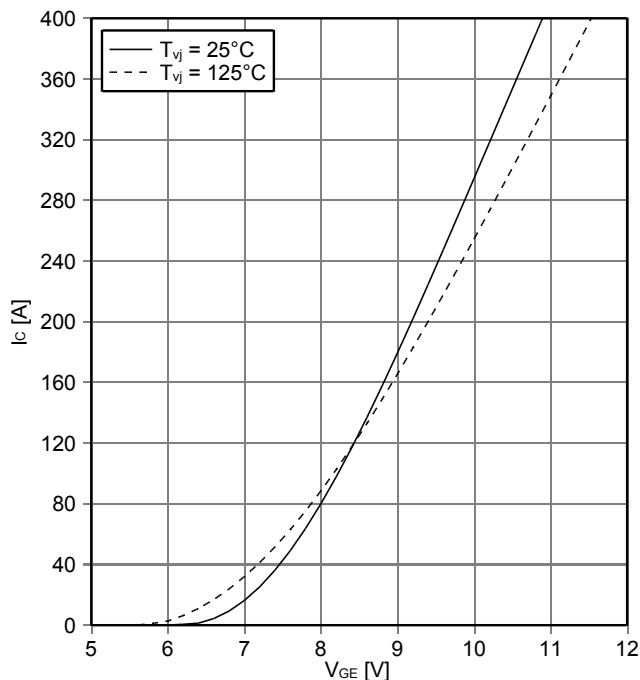
输出特性 IGBT, 逆变器 (典型)  
output characteristic IGBT, Inverter (typical)

$I_c = f(V_{CE})$   
 $T_{vj} = 125^\circ\text{C}$



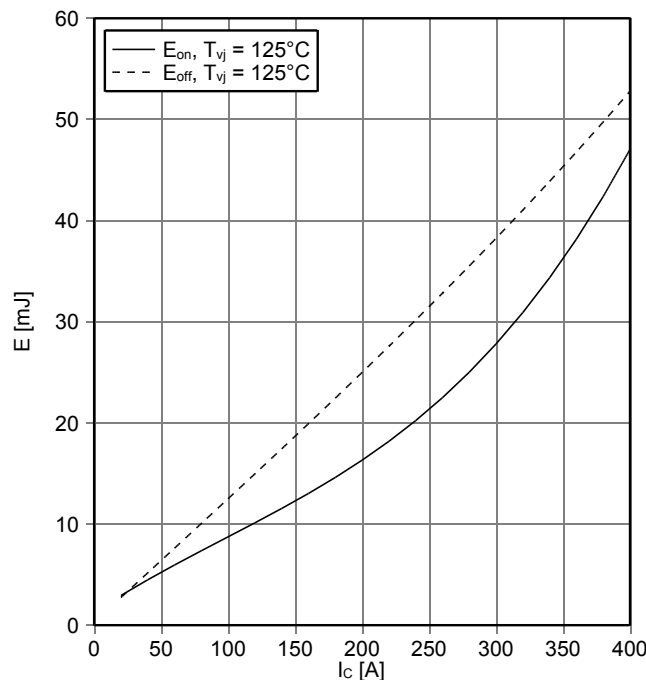
传输特性 IGBT, 逆变器 (典型)  
transfer characteristic IGBT, Inverter (typical)

$I_c = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)  
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_c), E_{off} = f(I_c)$   
 $V_{GE} = \pm 15\text{ V}, R_{Gon} = 3.6\ \Omega, R_{Goff} = 3.6\ \Omega, V_{CE} = 600\text{ V}$

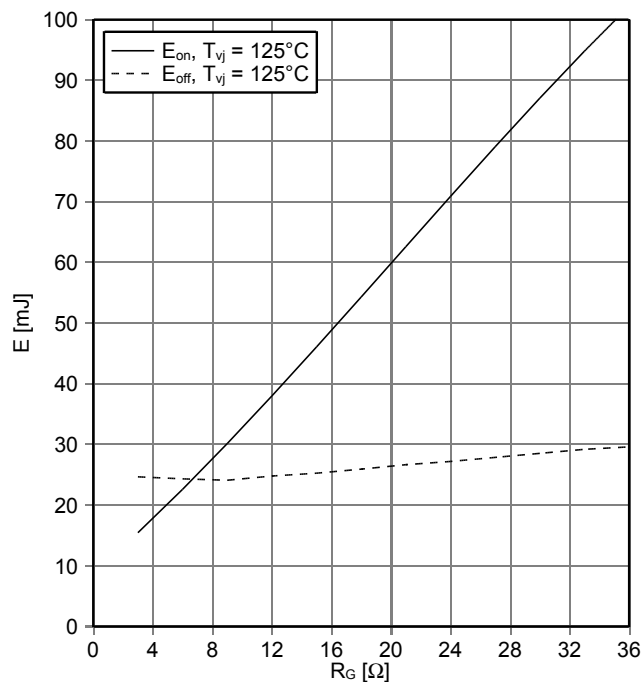


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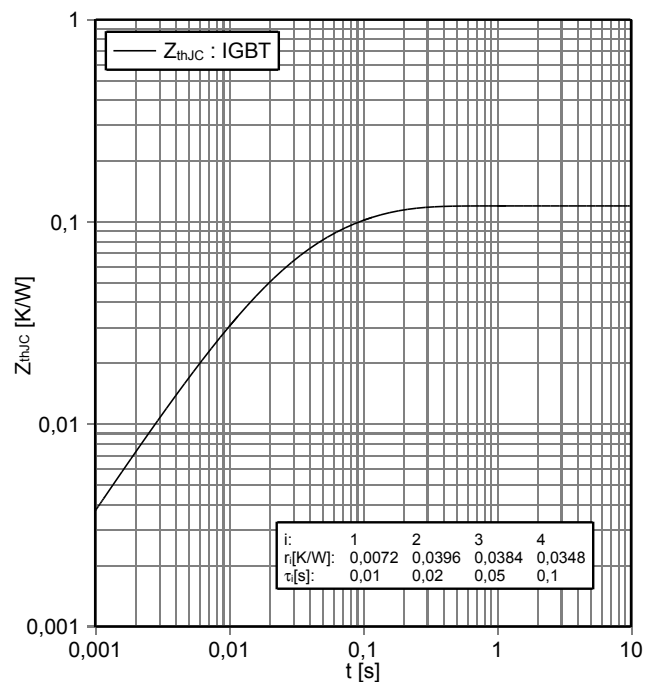
**开关损耗 IGBT, 逆变器 (典型)**  
**switching losses IGBT, Inverter (typical)**

$E_{on} = f(R_G), E_{off} = f(R_G)$   
 $V_{GE} = \pm 15\text{ V}, I_C = 200\text{ A}, V_{CE} = 600\text{ V}$



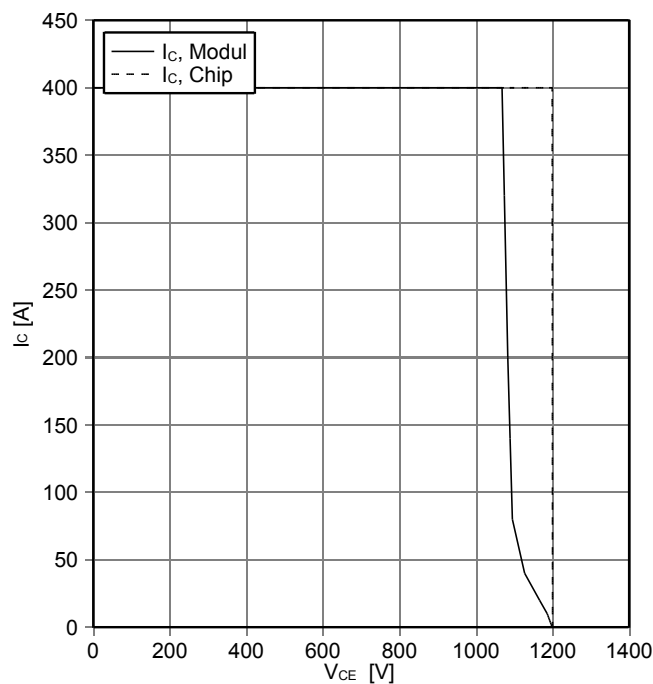
**瞬态热阻抗 IGBT, 逆变器**  
**transient thermal impedance IGBT, Inverter**

$Z_{thJC} = f(t)$



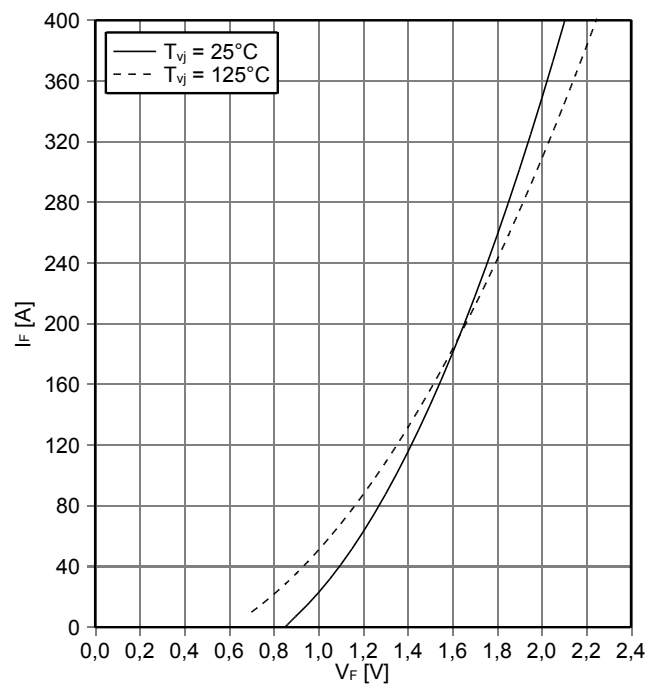
**反偏安全工作区 IGBT, 逆变器 (RBSOA)**  
**reverse bias safe operating area IGBT, Inverter (RBSOA)**

$I_C = f(V_{CE})$   
 $V_{GE} = \pm 15\text{ V}, R_{Goff} = 3.6\ \Omega, T_{vj} = 125^\circ\text{C}$



**正向偏压特性 二极管, 逆变器 (典型)**  
**forward characteristic of Diode, Inverter (typical)**

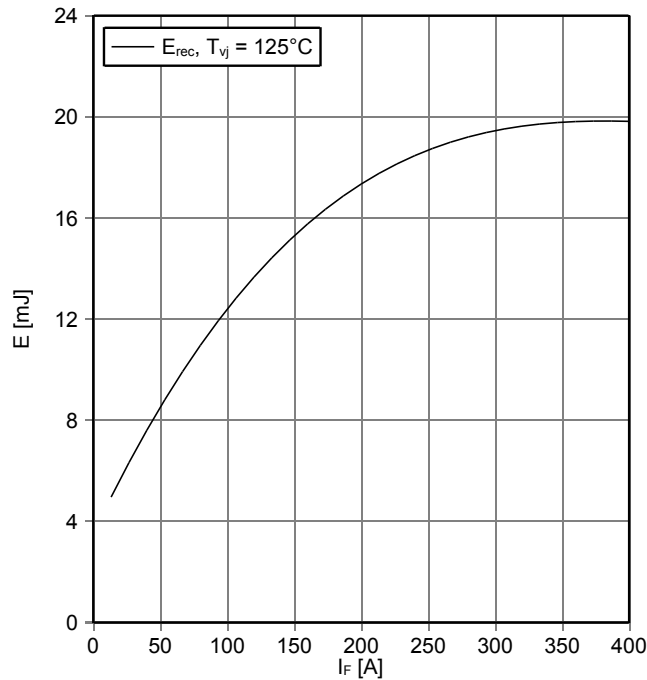
$I_F = f(V_F)$



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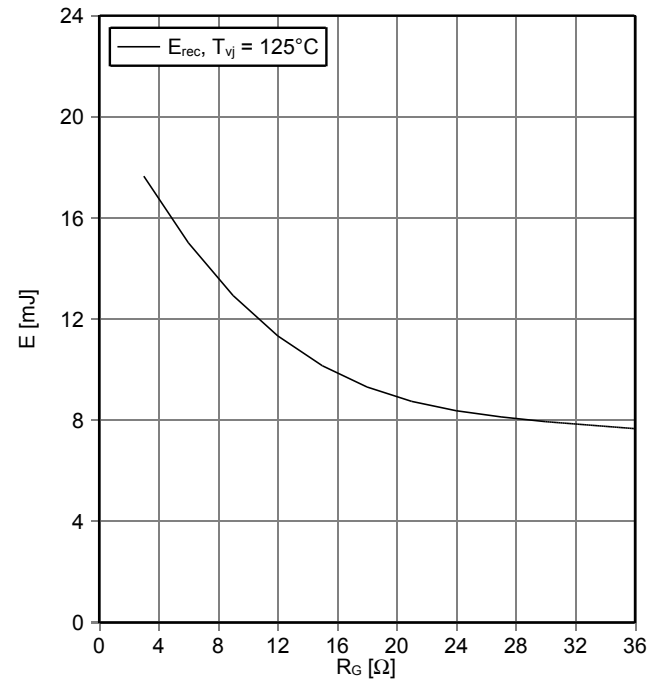
开关损耗 二极管, 逆变器 (典型)  
switching losses Diode, Inverter (typical)

$E_{rec} = f(I_F)$   
 $R_{Gon} = 3.6 \Omega, V_{CE} = 600 V$



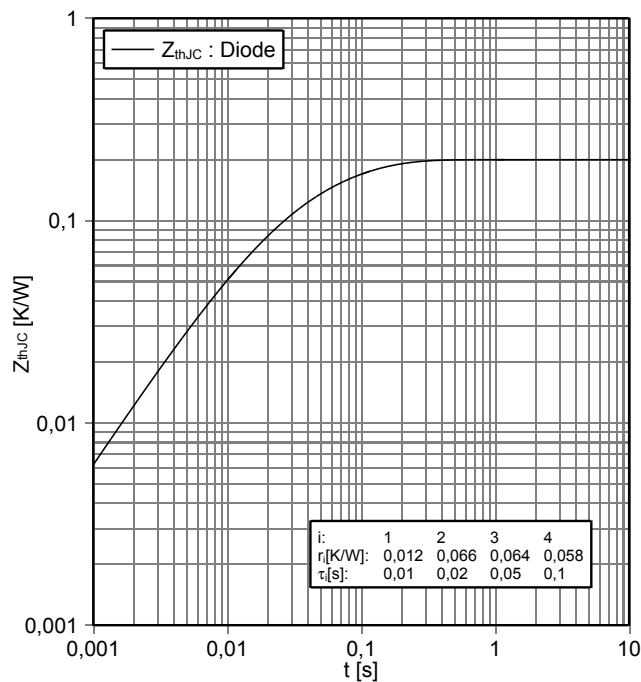
开关损耗 二极管, 逆变器 (典型)  
switching losses Diode, Inverter (typical)

$E_{rec} = f(R_G)$   
 $I_F = 200 A, V_{CE} = 600 V$



瞬态热阻抗 二极管, 逆变器  
transient thermal impedance Diode, Inverter

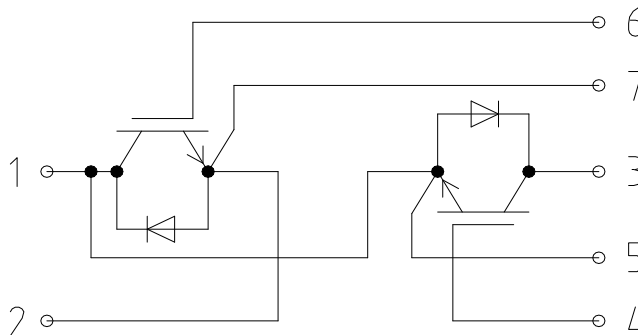
$Z_{thJC} = f(t)$



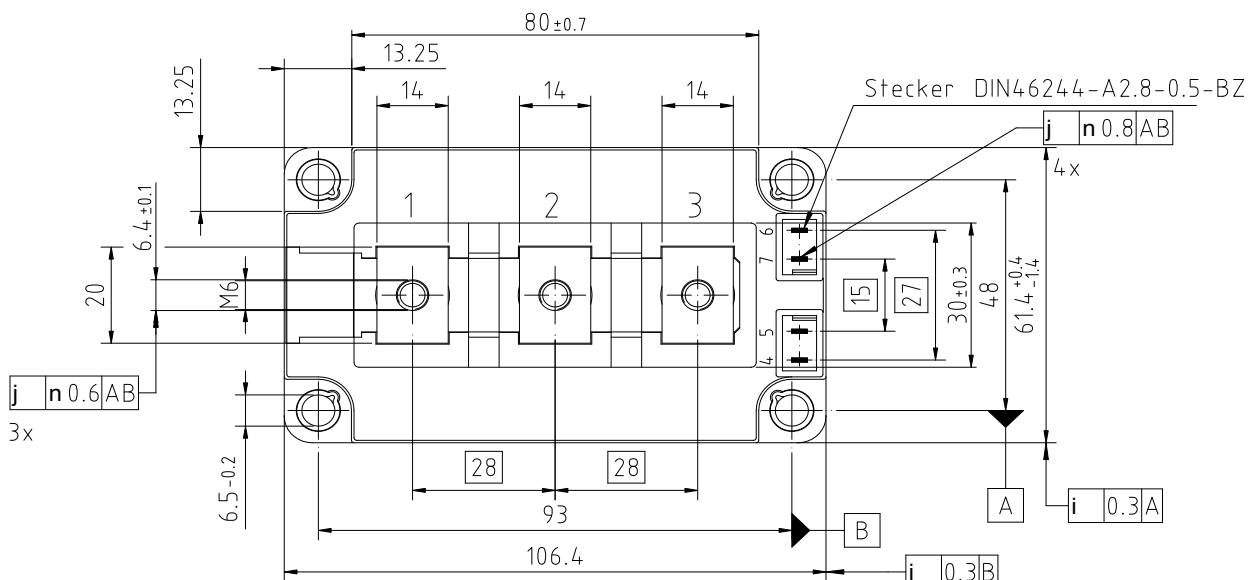
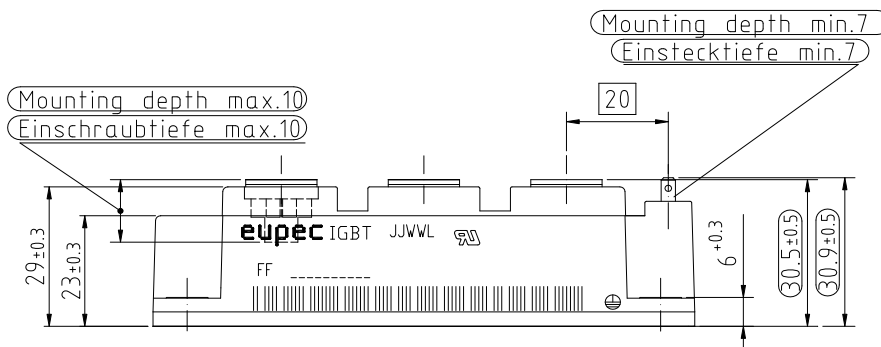
i:	1	2	3	4
r <sub>i</sub> [K/W]:	0,012	0,066	0,064	0,058
τ <sub>i</sub> [s]:	0,01	0,02	0,05	0,1

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接线图 / circuit\_diagram\_headline



封装尺寸 / package outlines



Freimaßtoleranzen  
nach ISO2768 mH

General tolerance  
ISO2768 mH

Az24

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**使用条件和条款**

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